



### **60V N-Channel Enhancement Mode MOSFET**

Current

Voltage

#### Features

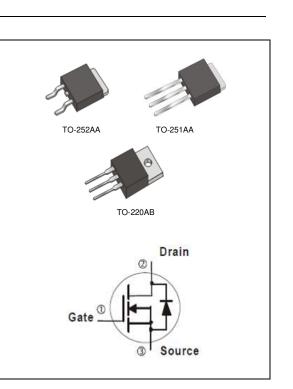
- $R_{DS(ON)}, V_{GS}@10V, I_D@20A<21m\Omega$
- $R_{DS(ON)}$ ,  $V_{GS}$ @4.5V,  $I_D$ @12A<24m $\Omega$
- High switching speed
- Improved dv/dt capability
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2.0

60 V

• Green molding compound as per IEC 61249 standard

#### **Mechanical Data**

- Case : TO-251AA, TO-252AA , TO-220AB Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- TO-251AA Approx. Weight : 0.0104 ounces, 0.297grams
- TO-252AA Approx. Weight : 0.0105 ounces, 0.297grams
- TO-220AB Approx. Weight : 0.067 ounces, 2 grams



**Maximum Ratings and Thermal Characteristics** (T<sub>A</sub>=25<sup>°</sup>C unless otherwise noted)

35 A

PARAMETER		SYMBOL	TO-251AA	TO-220AB	TO-252AA	UNITS	
Drain-Source Voltage		V <sub>DS</sub>	60			- v	
Gate-Source Voltage		V <sub>GS</sub>	<u>+</u> 20				
Continuous Drain Current	T <sub>C</sub> =25°C	- I <sub>D</sub>	35			Α	
	$T_{\rm C}=100^{\circ}{\rm C}$						
Pulsed Drain Current (Note 1)	T <sub>C</sub> =25°C	I <sub>DM</sub>	140				
Power Dissipation	T <sub>C</sub> =25°C	PD	63	104	63	w	
	$T_{\rm C}=100^{\circ}{\rm C}$		25	42	25		
Continuous Drain Current	T <sub>A</sub> =25°C	1	4.7			A	
	T <sub>A</sub> =70°C	I <sub>D</sub>	3.8				
Power Dissipation	T <sub>A</sub> =25°C	D-	1.1	2.0	1.1	14/	
Power Dissipation	T <sub>A</sub> =70°C	PD	0.7	1.3	0.7	W	
Single Pulse Avalanche Energy (Note 6)		E <sub>AS</sub>	42			mJ	
Operating Junction and		T <sub>J</sub> ,T <sub>STG</sub>	-55~150			°C	
Storage Temperature Range							
Typical Thermal Resistance <sup>(Note</sup>	e 4,5)						
- Junction to Case		$R_{ extsf{ heta}JC}$	2	1.2	2	°C/W	
<ul> <li>Junction to Ambient</li> <li>Limited only By Maximum Junction Temp</li> </ul>		$R_{\theta JA}$	110	62	110		





# **Electrical Characteristics** (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	60	-	-	v
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS}$ , $I_{D}=250$ uA	1	1.73	2.5	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	$V_{GS}$ =10V, $I_{D}$ =20A	-	17	21	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =12A	-	20	24	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS}$ =60V, $V_{GS}$ =0V	-	-	1	uA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = <u>+</u> 20V, V <sub>DS</sub> =0V	-	-	<u>+</u> 100	nA
Dynamic (Note 7)						
Total Gate Charge	Qg	V <sub>DS</sub> =30V, I <sub>D</sub> =15A, V <sub>GS</sub> =10V <sup>(Note 1,2)</sup>	-	28	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	3.5	-	
Gate-Drain Charge	Q <sub>gd</sub>		-	6.5	-	
Input Capacitance	Ciss		-	1680	-	
Output Capacitance	Coss	Coss V <sub>DS</sub> =20V, V <sub>GS</sub> =0V,		115	-	pF
Reverse Transfer Capacitance	Crss	f=1.0MHZ	-	85	-	
Turn-On Delay Time	td <sub>(on)</sub>		-	7.2	-	
Turn-On Rise Time	$v_{DD}=30v, I_D=IA,$		-	38	-	
Turn-Off Delay Time	td <sub>(off)</sub>	V <sub>GS</sub> =10V, R <sub>G</sub> =6Ω (Note 1,2)	-	34	-	ns
Turn-Off Fall Time	t <sub>f</sub>		-	8.2	-	
Drain-Source Diode						
Maximum Continuous Drain-Source			-	-	35	A
Diode Forward Current	۱ <sub>S</sub>					
Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> =1A, V <sub>GS</sub> =0V	-	0.67	1	V

NOTES :

- 1. Pulse width <300us, Duty cycle <2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature  $T_{J(MAX)}=150$  °C. Ratings are based on low frequency and duty cycles to keep initial  $T_J = 25$  °C.
- 4. The maximum current rating is package limited.
- 5.  $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz.square pad of copper.
- 6. The test condition is L=0.1mH,  $I_{AS}$ =29A,  $V_{DD}$ =25V,  $V_{GS}$ =10V,  $R_G$ =25ohm, Starting  $T_J$ =25°C
- 7. Guaranteed by design, not subject to production testing.

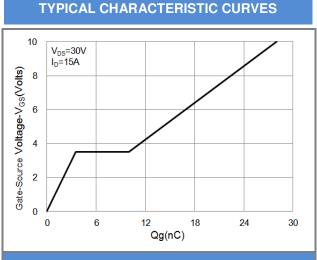




#### PJU35N06A / PJD35N06A / PJP35N06A **TYPICAL CHARACTERISTIC CURVES** 20 20 10V,8V,5V,4V $V_{DS}=5V$ V<sub>GS</sub>=3.5V I<sub>DS</sub>-Drain-to-S ource Current(A) I<sub>DS</sub>-Drain-to-Source Current(A) 15 15 10 10 V<sub>GS</sub>=3V T\_=125℃ T\_=25℃ 5 5 0 0 0 2 3 5 1 1.6 2.2 2.8 3.4 4 1 V<sub>DS</sub>-Drain-to-Source Voltage(V) V<sub>GS</sub>-Gate-to-Source Voltage(V) **Fig.1 Output Characteristics Fig.2 Transfer Characteristics** 27 2.5 R<sub>DS</sub>(on)- On-Resistance (Normalized) $R_{DS}(on)$ - On-Resistance(m $\Omega$ ) 24 2.0 V<sub>GS</sub>= 4.5V V<sub>GS</sub>=10V, I<sub>D</sub>=20A 21 1.5 V<sub>GS</sub>=4.5V, I<sub>D</sub>=12A $V_{GS} = 10V$ 1.0 18 0.5 15 25 175 0 50 75 100 125 150 0 5 10 15 20 Temperature (°C) I<sub>DS</sub>-Drain-to-Source Current(A) Fig.3 On-Resistance vs. Drain Current Fig.4 On-Resistance vs. Junction temperature 2500 10 V<sub>GS</sub> = 0V f = 1MHz Is-Source to-Drain Current(A) 2000 Ciss 1 Capacitance (pF) 1500 1000 Tj=25℃ T<sub>j</sub>=125℃ 0.1 500 Coss Crss 0 0.01 0 10 20 30 40 50 0 0.3 0.6 0.9 1.2 V<sub>DS</sub>-Drain-Source Voltage (V) V<sub>SD</sub>-Source-to-Drain Voltage(V) Fig.5 Capacitance vs. Drain-Source Voltage Fig.6 Source-Drain Diode Forward Voltage









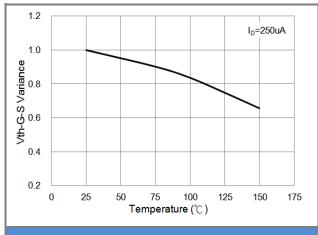
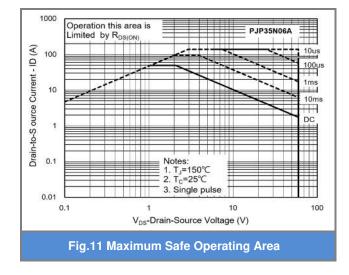
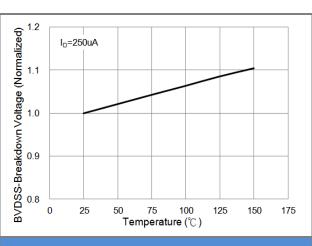


Fig.9 Threshold Voltage Variation with Temperature







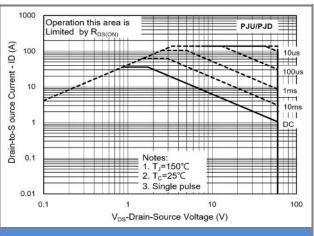
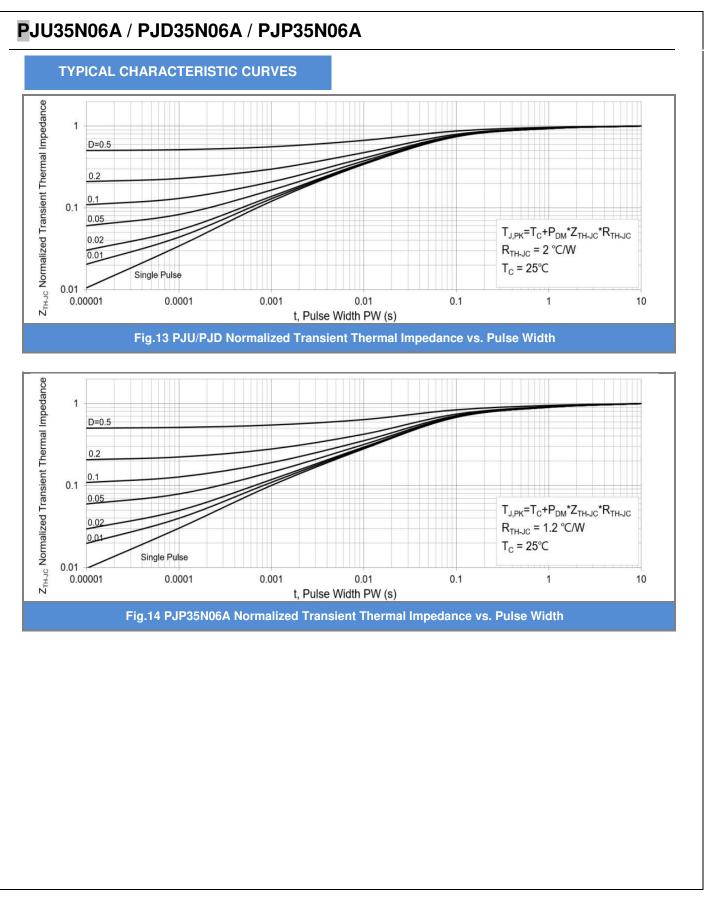


Fig.10 Maximum Safe Operating Area

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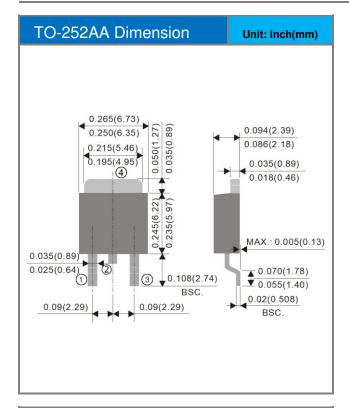


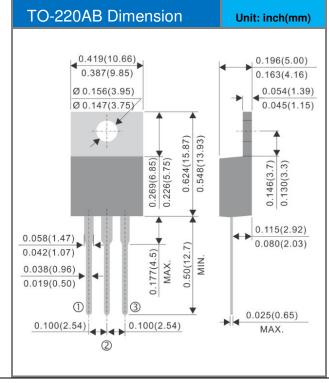


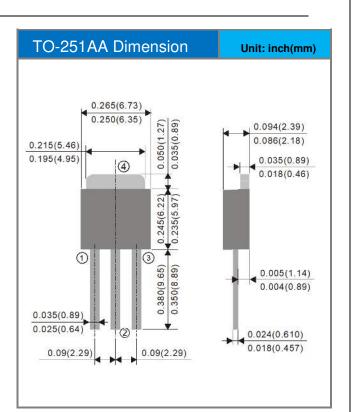




#### **Packaging Information**







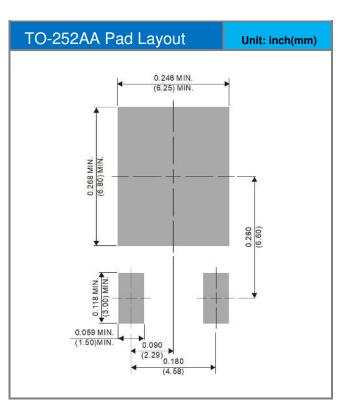




#### Part No Packing Code Version

Part No Packing Code	Package Type	Packing Type	Marking	Version
PJU35N06A_T0_00001	TO-251AA	80pcs / Tube	U35N06A	Halogen free
PJD35N06A_L2_00001	TO-252AA	3,000pcs / 13" reel	D35N06A	Halogen free
PJP35N06A_T0_00001	TO-220AB	50pcs / Tube	P35N06A	Halogen free

## **Mounting Pad Layout**







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